

# Enhancement Mode N-Channel Power MOSFET

## Features

- ◆ Ultra-fast and robust body diode
- ◆ Low  $R_{DS(on)}$  & FOM
- ◆ Excellent low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive

## Applications

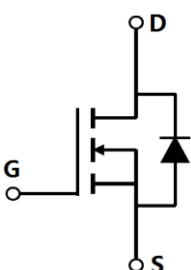
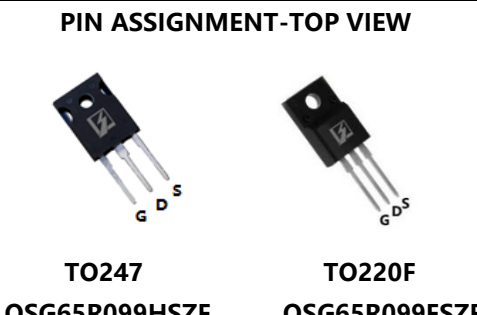
- ◆ PC power
- ◆ Server power supply
- ◆ Telecom
- ◆ Solar inverter
- ◆ Super charger for automobiles

## ■ General Description

OSG65R099xSZF use advanced GreenMOS™ technology to provide low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. This device offers extremely fast and robust body diode, and is suitable for telecom and super charger applications.

◆ $V_{DS, min@Tjmax}$	700 V
◆ $I_{D, pulse}$	96 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	99 mΩ
◆ $Q_g$	66.6 nC

## ■ Schematic and Package Information

SCHEMATIC DIAGRAM	PIN ASSIGNMENT-TOP VIEW
	

## ■ Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	650	V
Gate source voltage	$V_{GS}$	$\pm 30$	V
Continuous drain current <sup>1)</sup> , $T_C=25^\circ\text{C}$	$I_D$	32	A
Continuous drain current <sup>1)</sup> , $T_C=100^\circ\text{C}$		20	
Pulsed drain current <sup>2)</sup> , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	96	A
Power dissipation <sup>3)</sup> for TO247, $T_C=25^\circ\text{C}$	$P_D$	278	W
Power dissipation <sup>3)</sup> for TO220F, $T_C=25^\circ\text{C}$		35	
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	1000	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$ , $I_{SD}\leq I_D$	dv/dt	50	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	$^\circ\text{C}$

## ■ Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO247	TO220F	
Thermal resistance, junction-case	$R_{\theta JC}$	0.45	3.6	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62	62.5	$^{\circ}\text{C}/\text{W}$

## ■ Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	650			V	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$
		700				$V_{GS}=0\text{ V}, I_D=1\text{ mA}$ $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	3.0		4.5	V	$V_{DS}=V_{GS}, I_D=1\text{ mA}$
Drain-source on-state resistance	$R_{DS(on)}$		0.090	0.099	$\Omega$	$V_{GS}=10\text{ V}, I_D=16\text{ A}$
			0.21			$V_{GS}=10\text{ V}, I_D=16\text{ A},$ $T_j=150^{\circ}\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	$I_{DSS}$			10	$\mu\text{A}$	$V_{DS}=650\text{ V}, V_{GS}=0\text{ V}$

## ■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		3988.2		pF	$V_{GS}=0\text{ V},$ $V_{DS}=50\text{ V},$ $f=100\text{ kHz}$
Output capacitance	$C_{oss}$		210.4		pF	
Reverse transfer capacitance	$C_{rss}$		7.4		pF	
Turn-on delay time	$t_{d(on)}$		46.0		ns	$V_{GS}=10\text{ V},$ $V_{DS}=400\text{ V},$ $R_G=2\ \Omega,$ $I_D=20\text{ A}$
Rise time	$t_r$		60.3		ns	
Turn-off delay time	$t_{d(off)}$		93.0		ns	
Fall time	$t_f$		3.7		ns	

## ■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		66.6		nC	$I_D=20\text{ A}$ , $V_{DS}=400\text{ V}$ , $V_{GS}=10\text{ V}$
Gate-source charge	$Q_{gs}$		20.6		nC	
Gate-drain charge	$Q_{gd}$		24.8		nC	
Gate plateau voltage	$V_{\text{plateau}}$		6.7		V	

## ■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward current	$I_S$			32	A	$V_{GS}<V_{th}$
Pulsed source current	$I_{SP}$			96		
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=32\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		151.7		ns	$I_S=20\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		1.0		$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$		12.3		A	

## ■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=100\text{ V}$ ,  $R_G=50\text{ }\Omega$ ,  $L=80\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

■ **Electrical Characteristics Diagrams**

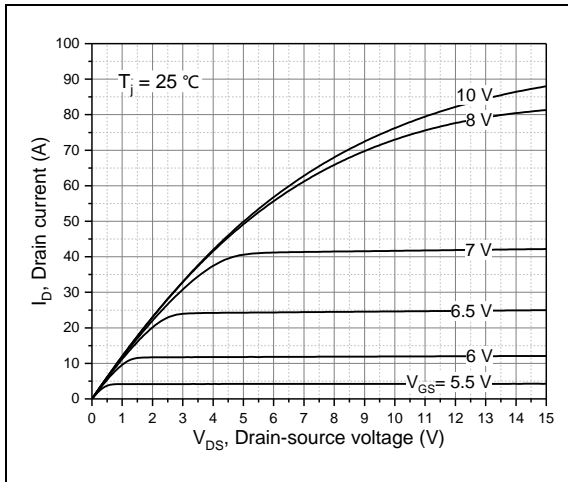


Figure 1, Typ. output characteristics

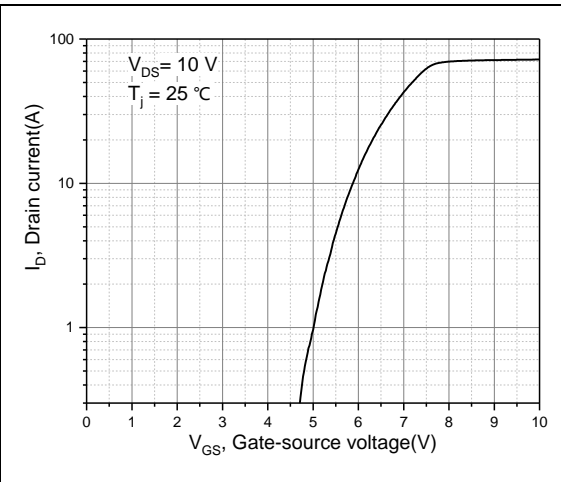


Figure 2, Typ. transfer characteristics

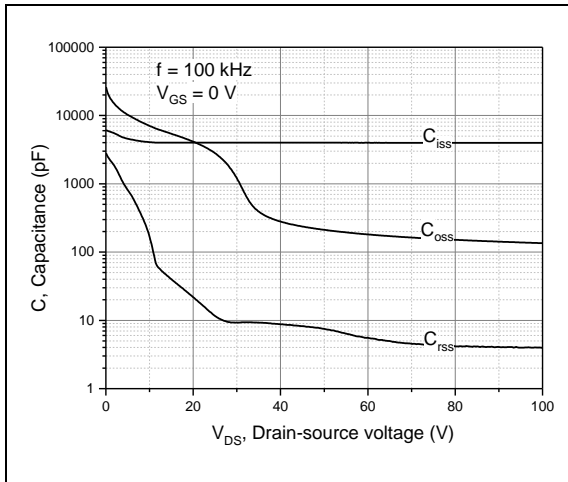


Figure 3, Typ. capacitances

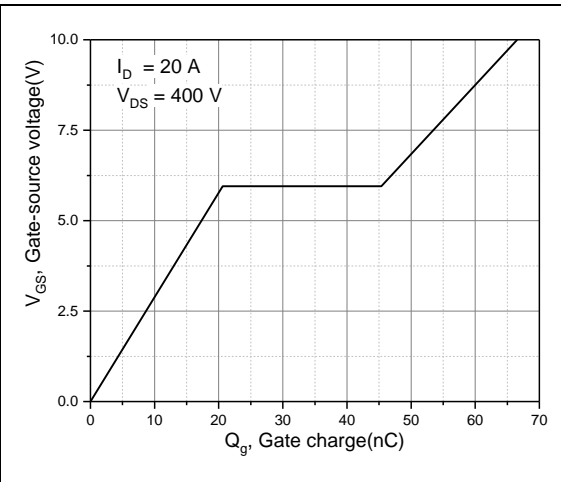


Figure 4, Typ. gate charge

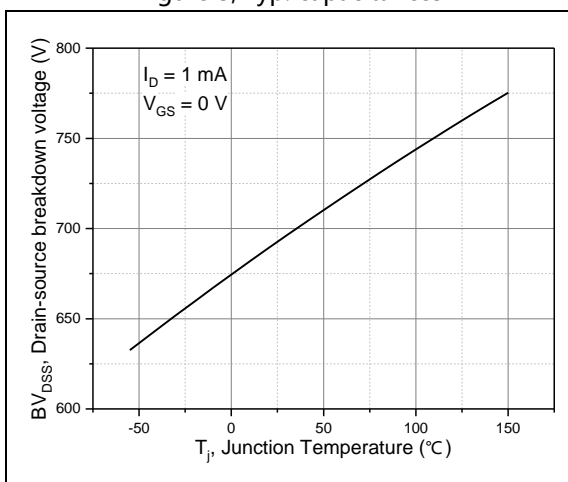


Figure 5, Drain-source breakdown voltage

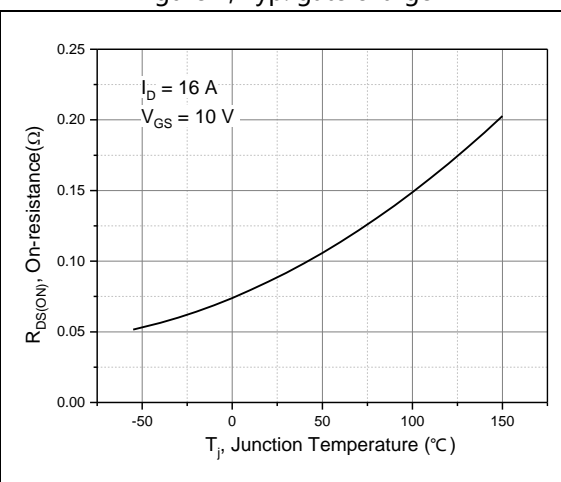


Figure 6, Drain-source on-state resistance

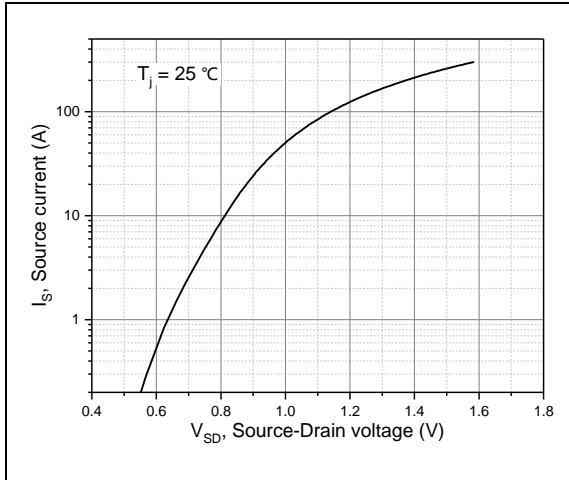


Figure 7, Forward characteristic of body diode

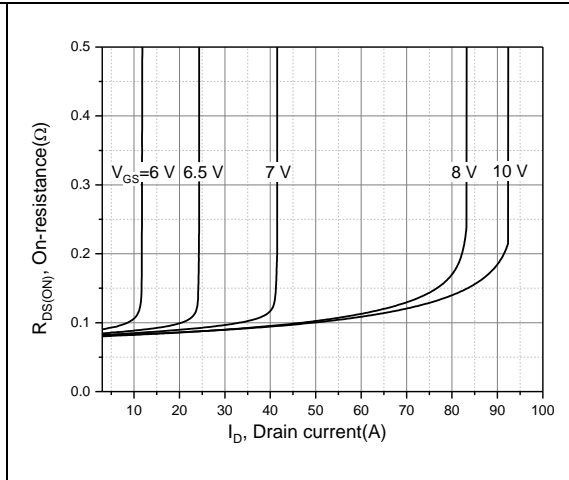


Figure 8, Drain-source on-state resistance

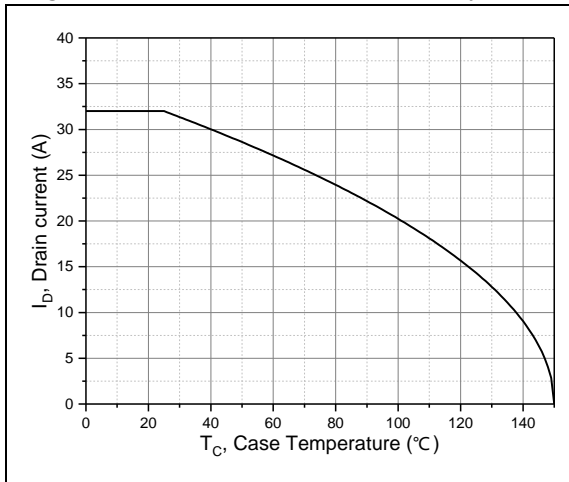


Figure 9, Drain current

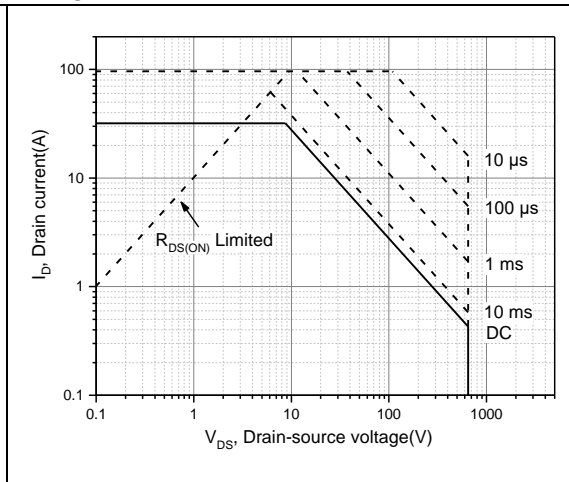


Figure 10, Safe operation area for TO247  
 $T_C=25\text{ }^\circ\text{C}$

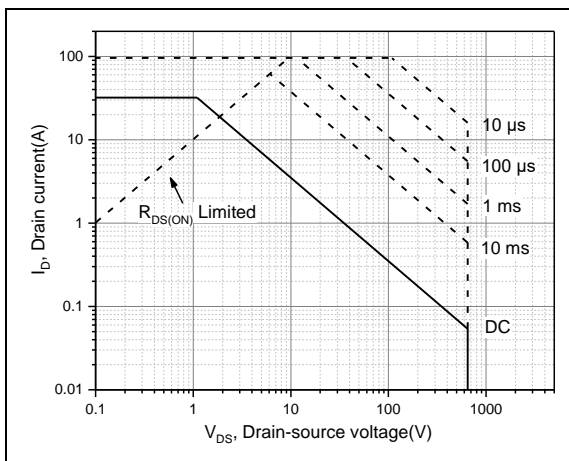


Figure 11, Safe operation area for TO220F  
 $T_C=25\text{ }^\circ\text{C}$

■ Test circuits and waveforms

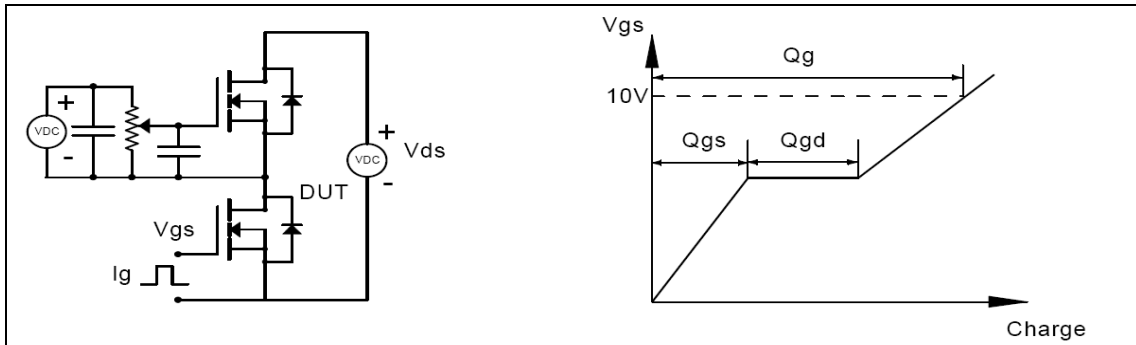


Figure 1, Gate charge test circuit & waveform

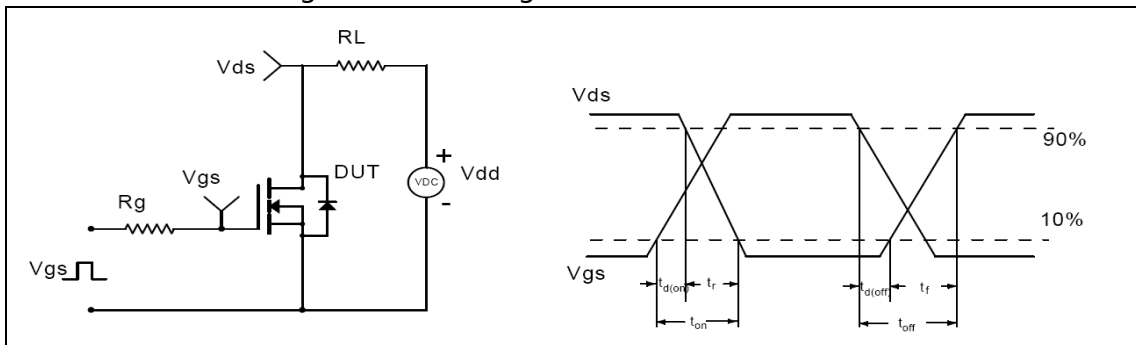


Figure 2, Switching time test circuit & waveforms

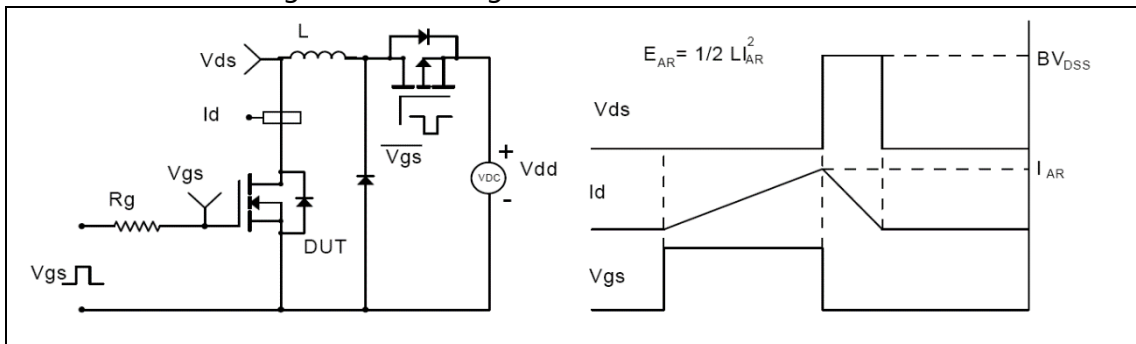


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

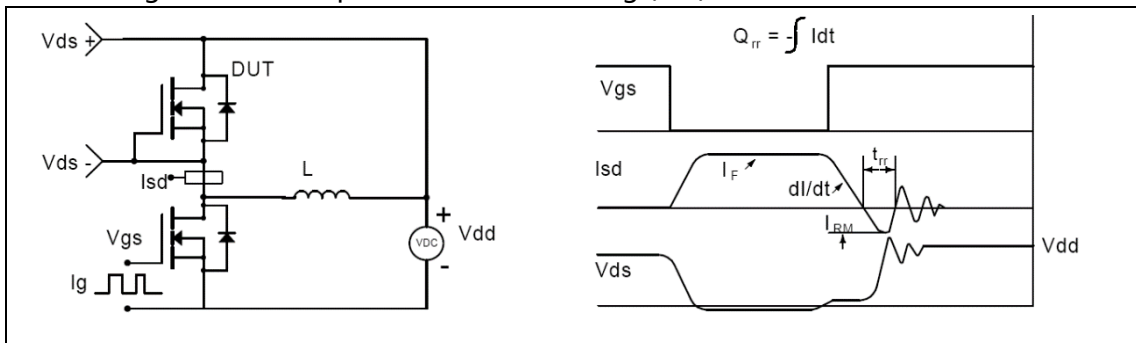
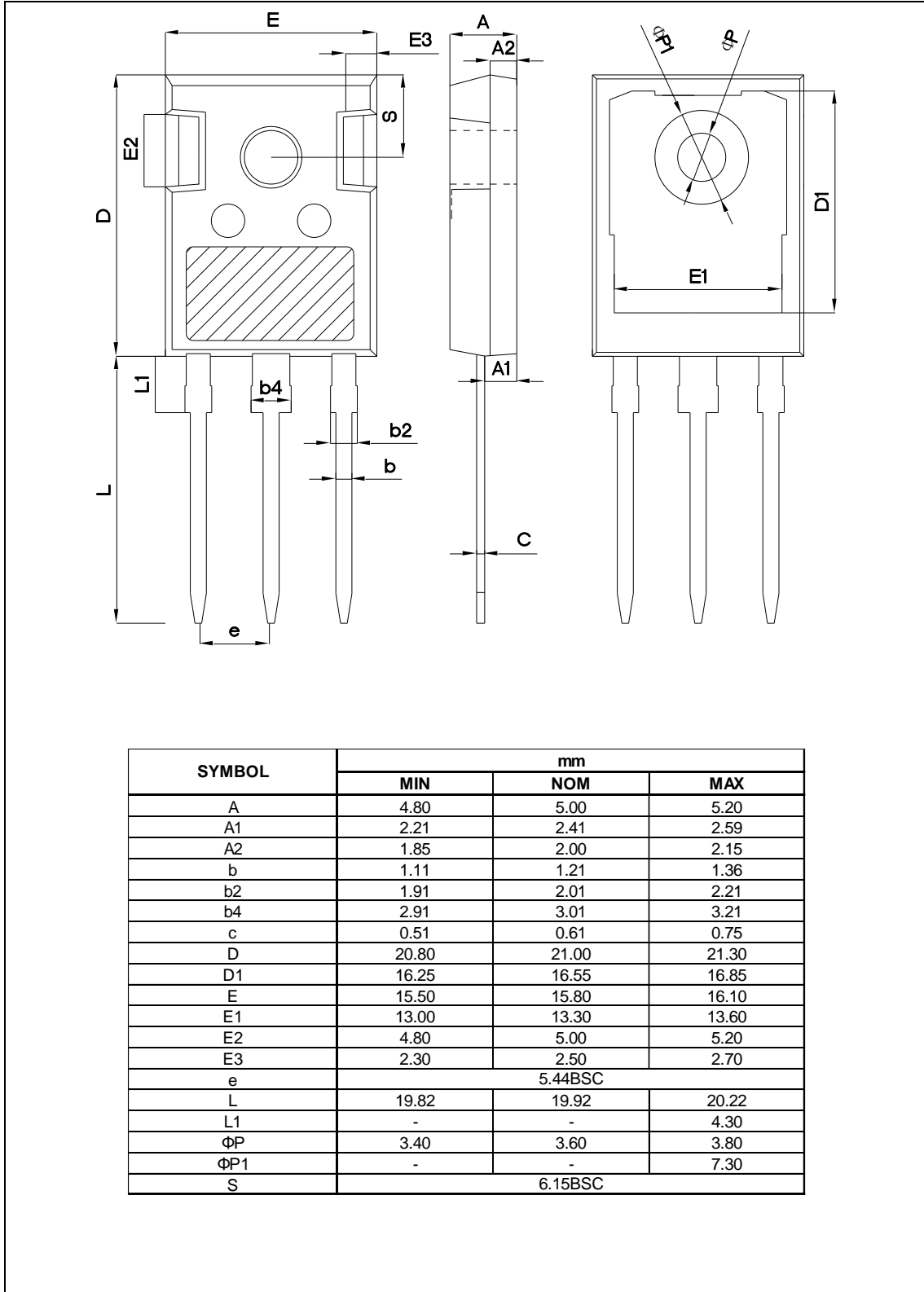


Figure 4, Diode reverse recovery test circuit & waveforms

**■ Package Information**

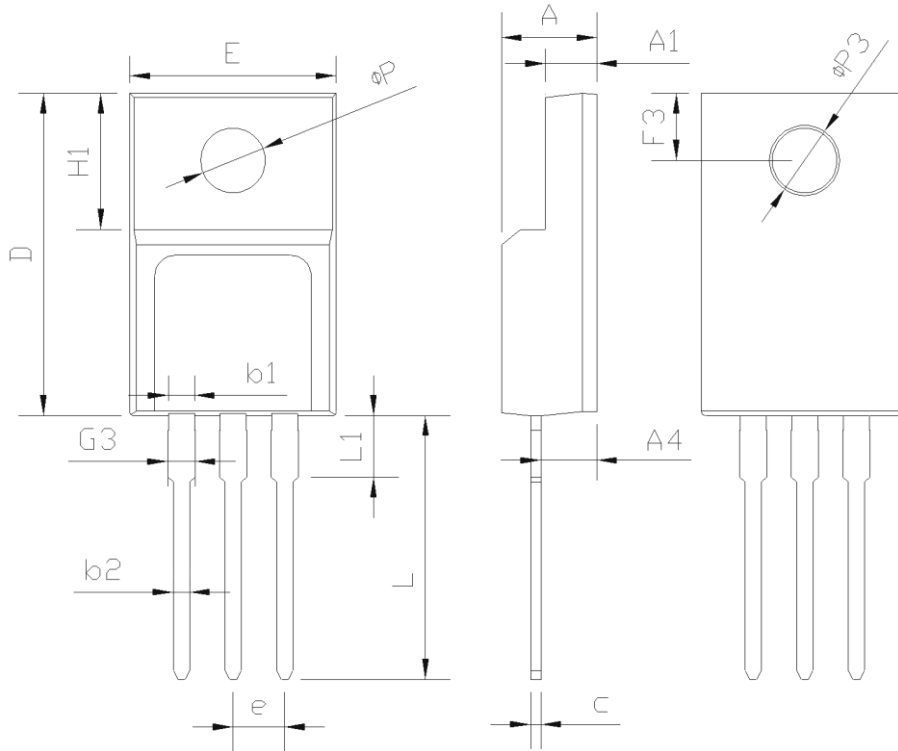
Figure1, TO247 package outline dimension





**■ Package Information**

Figure2, TO220F package outline dimension



SYMBOL	mm		
	MIN	NOM	MAX
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.88	3.03	3.18
ΦP	3.03	3.18	3.38
ΦP3	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95

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**■ Ordering Information**

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Package	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO247	30	11	330	6	1980
TO220F	50	20	1000	6	6000

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**■ Product Information**

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Product	Package	Pb Free	RoHS	Halogen Free
OSG65R099HSZF	TO247	yes	yes	yes
OSG65R099FSZF	TO220F	yes	yes	yes